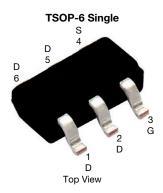




N-Channel 100 V (D-S) MOSFET

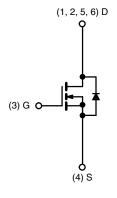


| PRODUCT SUMMARY | | | | | | |
|---|--------|--|--|--|--|--|
| V _{DS} (V) | 100 | | | | | |
| $R_{DS(on)}$ max. (Ω) at $V_{GS} = 10 \text{ V}$ | 0.170 | | | | | |
| $R_{DS(on)}$ max. (Ω) at $V_{GS} = 6 \text{ V}$ | 0.185 | | | | | |
| Q _g typ. (nC) | 5.5 | | | | | |
| I _D (A) | 2.4 | | | | | |
| Configuration | Single | | | | | |

FEATURES

- High-efficiency PWM optimized
- 100 % R_g tested
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912





N-Channel MOSFET

| ORDERING INFORMATION | |
|---------------------------------|-----------------|
| Package | TSOP-6 |
| Lead (Pb)-free | Si3430DV-T1-E3 |
| Lead (Pb)-free and halogen-free | Si3430DV-T1-GE3 |

| ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted) | | | | | | |
|--|------------------------|-----------------------------------|--------------|-------------|----|--|
| PARAMETER | SYMBOL | 5 s | STEADY STATE | UNIT | | |
| Drain-source voltage | V _{DS} | 100 | 100 | V | | |
| Gate-source voltage | V_{GS} | ± 20 | ± 20 | V | | |
| Continuous drain current (T _J = 175 °C) ^a | T _A = 25 °C | | 2.4 | 1.8 | Α | |
| | T _A = 85 °C | l _D | 1.7 | 1.3 | | |
| Pulsed drain current | I _{DM} | 8 | 8 | A | | |
| Avalanche current | L = 0.1 mH | I _{AR} | 6 | 6 | | |
| Repetitive avalanche energy (duty cycle ≤ 1 %) | L = U. I IIIII | E _{AR} | 1.8 | 1.8 | mJ | |
| Continuous source current (diode conduction) a | I _S | 1.7 | 1 | Α | | |
| Martin and a state of the form | T _A = 25 °C | Б | 2 | 1.14 | W | |
| Maximum power dissipation ^a | T _A = 85 °C | P _D | 1 | 0.59 | ** | |
| Operating junction and storage temperature range | 9 | T _J , T _{sta} | -55 to +150 | -55 to +150 | °C | |

| THERMAL RESISTANCE RATINGS | | | | | | |
|--|--------------|-------------------|---------|---------|------|--|
| PARAMETER | | SYMBOL | TYPICAL | MAXIMUM | UNIT | |
| Maximum junction-to-ambient ^a | t ≤ 5 s | R _{thJA} | 45 | 62.5 | °C/W | |
| | Steady state | | 90 | 110 | | |
| Maximum junction-to-foot (drain) | Steady state | Rt _{hJF} | 25 | 30 | | |

Note

a. Surface mounted on 1" x 1" FR4 board



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| SPECIFICATIONS (T _J = 25 °C, unless otherwise noted) | | | | | | | |
|---|---------------------|---|------|-------|-------|------|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNIT | |
| Static | | | | | | | |
| Gate threshold voltage | V _{GS(th)} | $V_{DS} = V_{DS}$, $I_D = 250 \mu A$ | 2 | - | 4.2 | V | |
| Gate-body leakage | I _{GSS} | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$ | - | - | ± 100 | nA | |
| Zero gate voltage drain current | 1 | $V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$ | - | - | 1 | μΑ | |
| Zero gate voltage drain current | I _{DSS} | V_{DS} = 80 V, V_{GS} = 0 V, T_J = 85 °C | - | - | 25 | | |
| On-state drain current a | I _{D(on)} | $V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$ | 8 | - | - | Α | |
| Drain-source on-state resistance a | В | $V_{GS} = 10 \text{ V}, I_D = 2.4 \text{ A}$ | - | 0.148 | 0.170 | Ω | |
| Drain-source on-state resistance " | R _{DS(on)} | $V_{GS} = 6 \text{ V}, I_D = 2.3 \text{ A}$ | - | 0.160 | 0.185 | | |
| Forward transconductance a | 9 _{fs} | $V_{DS} = 15 \text{ V}, I_D = 2.4 \text{ A}$ | - | 7 | - | S | |
| Diode forward voltage a | V _{SD} | I _S = 1.7 A, V _{GS} = 0 V | - | 0.8 | 1.2 | V | |
| Dynamic ^b | | | | | | | |
| Total gate charge | Q_{g} | | - | 5.5 | 8.2 | nC | |
| Gate-source charge | Q_{gs} | $V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 2.4 \text{ A}$ | - | 1.5 | - | | |
| Gate-drain charge | Q_{gd} | | - | 1.4 | - | | |
| Gate resistance | R_g | | 1 | - | 4 | Ω | |
| Turn-on delay time | t _{d(on)} | | - | 9 | 20 | | |
| Rise time | t _r | $V_{DD} = 50 \text{ V}, R_1 = 50 \Omega$ | - | 11 | 20 | ns | |
| Turn-off delay time | t _{d(off)} | $I_D\cong 1$ A, $V_{GEN}=10$ V, $R_g=6$ Ω | - | 16 | 30 | | |
| Fall time | t _f | | - | 9 | 20 | | |
| Gate resistance | Rg | V _{GS} = 0.1 V, f = 5 MHz | - | 2.8 | - | Ω | |
| Source-drain reverse recovery time | t _{rr} | I _F = 1.7 A, di/dt = 100 A/μs | - | 50 | 80 | ns | |

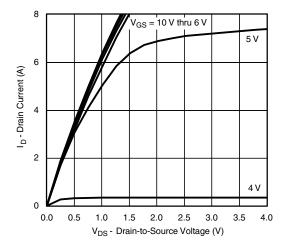
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing

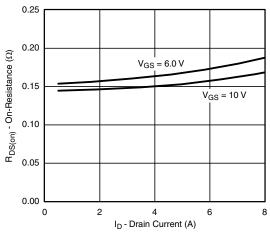
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



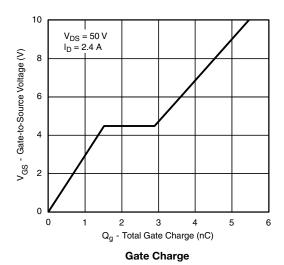
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

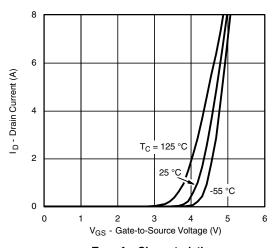


Output Characteristics

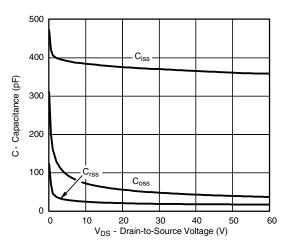


On-Resistance vs. Drain Current

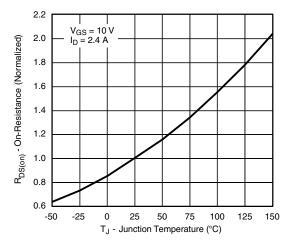




Transfer Characteristics



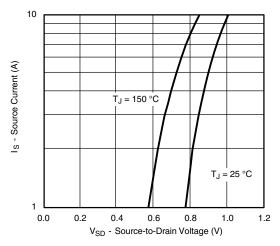
Capacitance



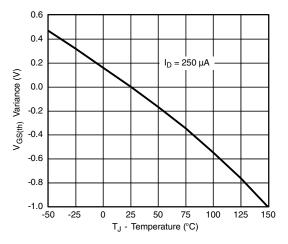
On-Resistance vs. Junction Temperature



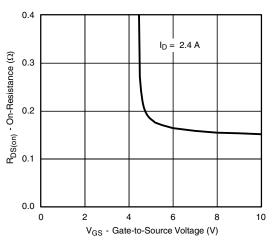
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



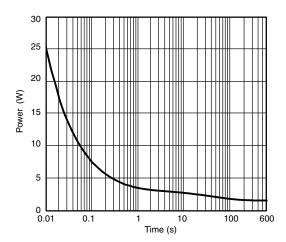
Source-Drain Diode Forward Voltage



Threshold Voltage



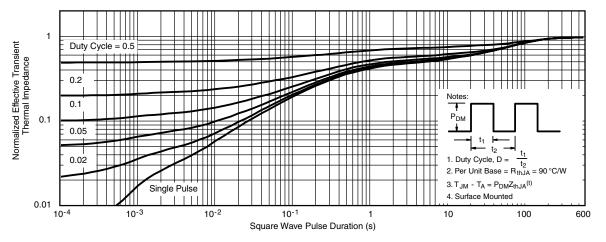
On-Resistance vs. Gate-to-Source Voltage



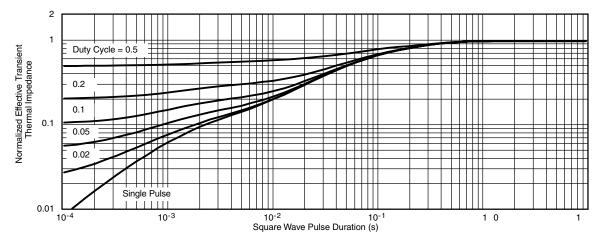
Single Pulse Power



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

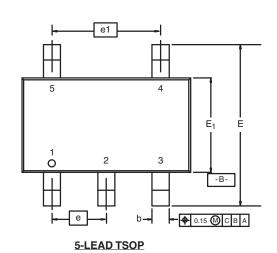
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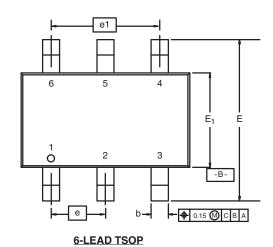


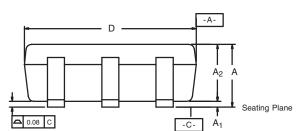


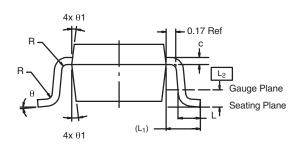
TSOP: 5/6-LEAD

JEDEC Part Number: MO-193C









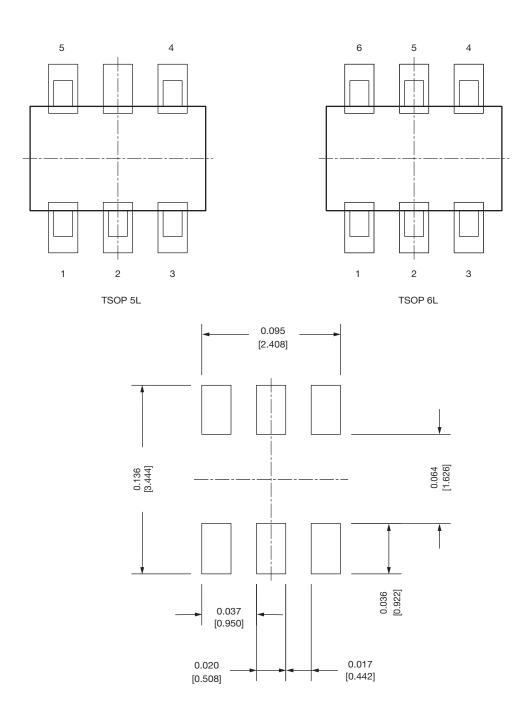
| | MILLIMETERS | | | INCHES | | | |
|---|-------------|----------|------|-------------|-------|-------|--|
| Dim | Min | Nom | Max | Min | Nom | Max | |
| Α | 0.91 | - | 1.10 | 0.036 | - | 0.043 | |
| A ₁ | 0.01 | - | 0.10 | 0.0004 | - | 0.004 | |
| A ₂ | 0.90 | - | 1.00 | 0.035 | 0.038 | 0.039 | |
| b | 0.30 | 0.32 | 0.45 | 0.012 | 0.013 | 0.018 | |
| С | 0.10 | 0.15 | 0.20 | 0.004 0.006 | | 0.008 | |
| D | 2.95 | 3.05 | 3.10 | 0.116 | 0.120 | 0.122 | |
| Е | 2.70 | 2.85 | 2.98 | 0.106 | 0.112 | 0.117 | |
| E ₁ | 1.55 | 1.65 | 1.70 | 0.061 | 0.065 | 0.067 | |
| е | | 0.95 BSC | | 0.0374 BSC | | | |
| e ₁ | 1.80 | 1.90 | 2.00 | 0.071 | 0.075 | 0.079 | |
| L | 0.32 | - | 0.50 | 0.012 | - | 0.020 | |
| L ₁ | | 0.60 Ref | | 0.024 Ref | | | |
| L ₂ | 0.25 BSC | | | 0.010 BSC | | | |
| R | 0.10 | - | - | 0.004 | - | - | |
| θ | 0° | 4° | 8° | 0° | 4° | 8° | |
| θ_1 | | 7° Nom | | 7° Nom | | | |
| ECN: C-06593-Rev. I, 18-Dec-06 DWG: 5540 | | | | | | | |

Document Number: 71200 18-Dec-06

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Recommended Land Pattern For TSOP-5L / TSOP-6L



Note

• All dimensions are in inches (millimeter)

ECN: C22-0860-Rev. B, 24-Oct-2022 DWG: 3010



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